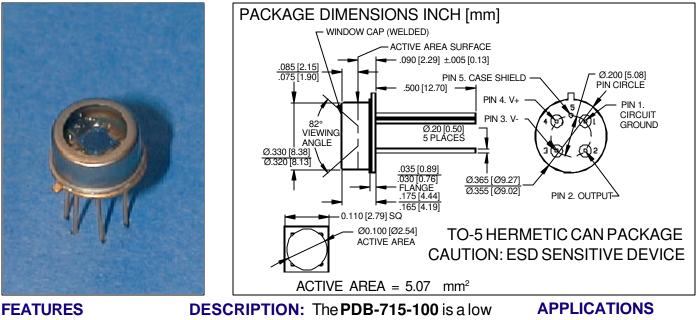
# PHOTONIC <u>DETECTORS INC.</u>

### Detector Amplifier Hybrid, Blue Enhanced (ref PDB-C715-100) Type PDB-715-100



- 10 Khz bandwidth
- Internal100 MOhm gain
- Low offset voltage
- Low input bias current

**DESCRIPTION:** The **PDB-715-100** is a low noise, medium speed, blue enhanced silicon photodiode integrated with a low noise JFET monolithic transimpedance op-amp. There is an internal 100 MOhm feedback gain resistor which limits the bandwidth to 10KHz.

- Medical diagnostic
- Low signal applications

0.6 0.5

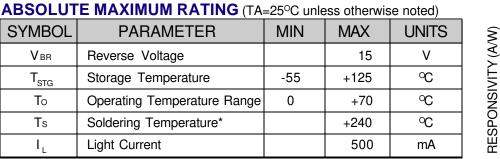
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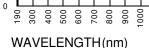
0.3

0.2 0.1

- Color analysis
- Analytical chemistry

## SPECTRALRESPONSE





100

200

\*1/16 inch from case for 3 secs max

#### PHOTODIODE ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	MIN	TYP	MAX	UNITS
lsc	Short Circuit Current	H = 100 fc, 2850 K	45	65		μA
ΙD	Dark Current	$H = 0, V_{R} = 10 V$		1.0	5.0	nA
Rsh	Shunt Resistance	$H = 0, V_{R} = 10 \text{ mV}$	.5	2		GΩ
TC Rsh	RSH Temp. Coefficient	$H = 0, V_{R} = 10 \text{ mV}$		-8		% / °C
CJ	Junction Capacitance	$H = 0, V_{R} = 10 V^{**}$		15		рF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λρ	Spectral Response - Peak	Spot Scan		950		nm
VBR	Breakdown Voltage	I = 10 µµA	100	125		V
NEP	Noise Equivalent Power	VR = 10 V @ Peak		2.5x10 <sup>-14</sup>		$W/\sqrt{Hz}$
tr	Response Time	$RL = 1 K\Omega V_R = 10 V$		15		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. \*\* f = 1 MHz PAGE 1 OF 2 [FORMNO.100-PDB-715-100 REVB]

# PHOTONIC DETECTORS INC.

### Detector Amplifier Hybrid (ref PDB-C715-100) Type PDB-715-100

AMPLIFIER SPECIFICATION TA = 25° C and VS =± 15 vdc UNLESS OTHERWISE NOTED

CHARACTERISTIC	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS	
FEEDBACK NETWORK 100 MEG $\Omega$ RESISTER, 1pF* CAPACITOR	THINFILMRESISTOR TRIMMED TO±5% *TOL ±5%		100		MEG Ω	
	INITIALOFFSET		0.75	2.0	mV	
INPUT OFFSET VOLTAGE	LONGTERMOFFSETSTABILITY		15		µV/MONTH	
INPUT BIAS CURRENT	RENT OFFSET CURRENT, VCM=0		5	20	рА	
INPUT IMPEDANCE	DIFFERENTIAL		1 X 10 <sup>-12</sup> ∥3			
	COMMONMODE		1 X 10 <sup>-12</sup> ∥3		- Ω <b>p</b> F	
	COMMONMODE	±11	±12	V		
INPUT VOLTAGE RANGE	COMMONMODE REJECTION VCM±10 V	76	90			
INPUT VOLTAGE NOISE	VOLTAGE 0, 1 Hz TO 10 Hz		2		μV p-p	
INPUT VOLTAGENOISE	VOLTAGE 0, f=10 Khz		30		nV∕√Hz	
INPUT CURRENTNOISE	f=1 Khz		1.8		fA / √Hz	
	UNITY GAIN, SMALL SIGNAL	0.8	1.0		MHz	
FREQUENCY RESPONSE	SLEW RATE, UNITY GAIN	1.0	1.8		V/µs	
OPEN LOOP GAIN	vo= $\pm 10$ V, R <sub>L</sub> =10 K $\Omega$	300	1000		V/mV	
OUTPUT CHARACTERISTICS	VOLTAGE @ $R_L = 10 K\Omega$	±12	±13		V	
	VOLTAGE @ $R_1 > 5 K \Omega$	±11	±12.3		V	
POWER SUPPLY	OPERATING RANGE	±4.5	±15	±18	V	

AMPLIFIER ABSOLUTE MAXIMUM RATIN	ן			
PARAMETER	MIN	MAX	UNITS	CASE SHIELD 1 PF
SUPPLYVOLTAGE	±4.5	±18	V	
INTERNAL POWER DISSIPATION		500	mW	5.1 mm <sup>e</sup> 2.5 mm DIA PHOTODIODE
STORAGETEMPERATURE	-55	+150	° C	
OPERATINGTEMPERATURE	0	+70	°C	PIN 1 -V- CIRCUIT GROUND

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